SiT9366

1 to 220 MHz Ultra-low Jitter Differential Oscillator

Features

- Any frequency between 1 MHz and 220 MHz accurate to 6 decimal places
- LVPECL, LVDS and HCSL output signaling
- 0.1ps RMS phase jitter (random) for Ethernet applications
- Contact SiTime for frequency stability as low as ±10 ppm
- Wide temperature range from -40°C to 85°C
  Contact SiTime for higher temperature range options
- Industry-standard packages: 3.2 x 2.5, 7.0 x 5.0 mm
  Contact SiTime for 5.0 x 3.2 mm package

Applications

- 10/40/100GB Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers

Electrical Characteristics

All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination show in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

Table 1. Electrical Characteristics – Common to LVPECL, LVDS and HCSL

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Frequency Range						
Output Frequency Range	f	1	–	220	MHz	Accurate to 6 decimal places
Frequency Stability						
Frequency Stability	F_stab	-10	–	+10	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations. Contact SiTime for ± 10 ppm.
		-20	–	+20	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations
		-25	–	+25	ppm	
		-50	–	+50	ppm	
First Year Aging	F_1y	–	±1	–	ppm	At 25°C
Temperature Range						
Operating Temperature Range	T_use	-20	–	+70	°C	Extended Commercial
		-40	–	+85	°C	Industrial. Contact SiTime for higher temperature range options
Supply Voltage						
Supply Voltage	Vdd	2.97	3.30	3.63	V	
		2.70	3.00	3.30	V	
		2.52	2.80	3.08	V	
		2.25	2.50	2.75	V	
Input Characteristics						
Input Voltage High	VIH	70%	–	–	Vdd	Pin 1, OE
Input Voltage Low	VIL	–	–	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	–	100	-	kΩ	Pin 1, OE logic high or logic low
Output Characteristics						
Duty Cycle	DC	45	–	55	%	
Startup and OE Timing						
Startup Time	T_start	–	–	3.0	ms	Measured from the time Vdd reaches its rated minimum value.
OE Enable/Disable Time	T_oe	–	–	3.8	µs	f = 156.25 MHz.

Table 2. Electrical Characteristics – LVPECL

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Maximum Output Current	I_driver	–	–	32	mA	Maximum average current drawn from OUT+ or OUT-
Output Characteristics						
Output High Voltage	VOH	Vdd-1.1	–	Vdd-0.7	V	See Figure 2
Output Low Voltage	VOL	Vdd-1.9	–	Vdd-1.5	V	See Figure 2
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 3
Rise/Fall Time	Tr, Tf	–	225	290	ps	20% to 80%, see Figure 2
Jitter						
RMS Phase Jitter (random)	T_phj	–	0.220	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 7.0 x 5.0 mm package.
		–	0.225	0.280	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 3.2 x 2.5 mm package.
		–	0.1	–	ps	f = 156.25, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds
RMS Period Jitter[1]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, VDD = 3.3V or 2.5V

Notes:
1. Measured according to JESD65B

Table 3. Electrical Characteristics – LVDS

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	79	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Output Characteristics						
Differential Output Voltage	VOD	250	–	450	mV	See Figure 4
VOD Magnitude Change	ΔVOD	–	–	50	mV	See Figure 4
Offset Voltage	VOS	1.125	–	1.375	V	See Figure 4
VOS Magnitude Change	ΔVOS	–	–	50	mV	See Figure 4
Rise/Fall Time	Tr, Tf	–	400	470	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 4
Jitter						
RMS Phase Jitter (random)	T_phj	–	0.215	0.265	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds. Includes spurs. 7.0 x 5.0 mm package.
		–	0.235	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 3.2 x 2.5 package.
		–	0.1	–	ps	f = 156.25, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds
RMS Period Jitter[2]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, VDD = 3.3V or 2.5V

Notes:
2. Measured according to JESD65B

Table 4. Electrical Characteristics – HCSL

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Current Consumption						
Current Consumption	Idd	–	–	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	–	–	58	mA	OE = Low
Output Disable Leakage Current	I_leak	–	0.15	–	µA	OE = Low
Maximum Output Current	I_driver	–	–	36	mA	Maximum average current drawn from OUT+ or OUT-
Output Characteristics						
Output High Voltage	VOH	0.60	–	0.90	V	See Figure 2
Output Low Voltage	VOL	-0.05	–	0.08	V	See Figure 2
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.8	V	See Figure 3
Rise/Fall Time	Tr, Tf	–	360	465	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 2
Jitter						
RMS Phase Jitter (random)	T_phj	–	0.220	0.270	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Includes spurs. Vdds, 7.0 x 5.0 mm package.
		–	0.230	0.275	ps	f = 156.25 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Includes spurs. Vdds, 7.0 x 5.0 mm package. 3.2 x 2.5 package = 0.275 ps.
		–	0.1	–	ps	f = 156.25, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds
RMS Period Jitter[3]	T_jitt	–	1.0	1.6	ps	f = 100, 156.25 or 212.5 MHz, VDD = 3.3V or 2.5V

Notes:
3. Measured according to JESD65B

Table 5. Pin Description

Pin	Map	Functionality	
1	OE/NC	Output Enable (OE)	H[4]: specified frequency output L: output is high impedance
		Non Connect (NC)	H or L or Open: No effect on output frequency or other device functions
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation
3	GND	Power	VDD Power Supply Ground
4	OUT+	Output	Oscillator output
5	OUT-	Output	Complementary oscillator output
6	VDD	Power	Power supply voltage[5]

Notes:
4. In OE mode, a pull-up resistor of 10 kΩ or less is recommended if pin 1 is not externally driven.
5. A capacitor of value 0.1 µF or higher between Vdd and GND is required. An additional 10 µF capacitor between Vdd and GND is required for the best phase jitter performance

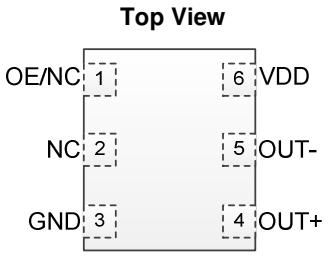


Figure 1. Pin Assignments

Table 6. Absolute Maximum Ratings

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part.
Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
VDD	-0.5	4.0	V
VIH		VDD + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	ºC
Maximum Junction Temperature		130	ºC
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	ºC

Table 7. Thermal Considerations[6]

Package	θ_{JA}, 4 Layer Board (°C/W)	θ_{JC}, Bottom (°C/W)
3225, 6-pin	80	30
7050, 6-pin	52	19

Notes:
6. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 8. Maximum Operating Junction Temperature[7]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C

Notes:
7. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 9. Environmental Compliance

Parameter	Test Conditions	Value	Unit
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	*g*
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	*g*
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C
Moisture Sensitivity Level	MSL1 @ 260°C		
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V
Charge-Device Model ESD Protection	JESD220C101	750	V
Latch-up Tolerance	JESD78 Compliant		

Waveform Diagrams

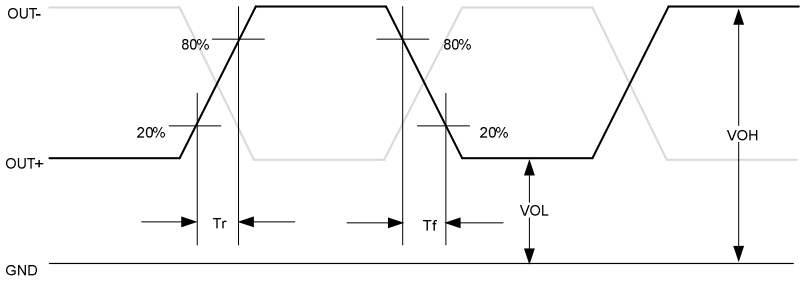


Figure 2. LVPECL/HCSL Voltage Levels per Differential Pin (OUT+/OUT-)

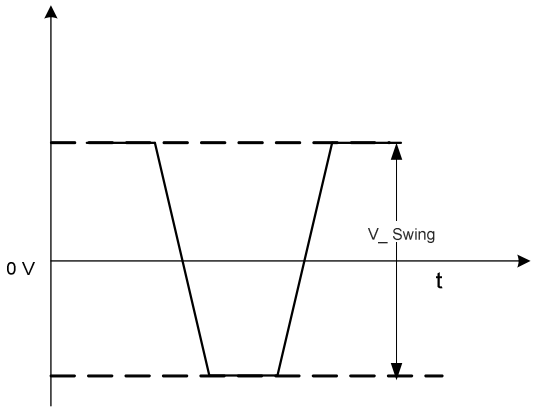


Figure 3. LVPECL/HCSL Voltage Levels across Differential Pair

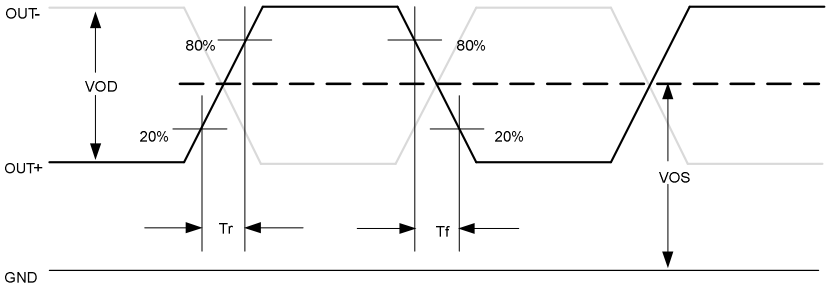


Figure 4. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)

Termination Diagrams

LVPECL:

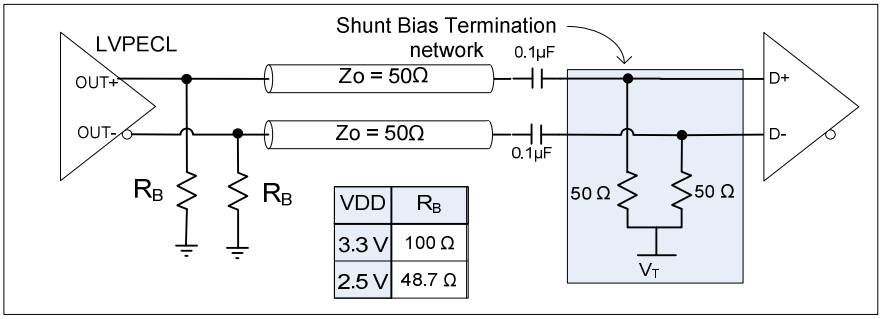


Figure 5: LVPECL with AC-coupled termination

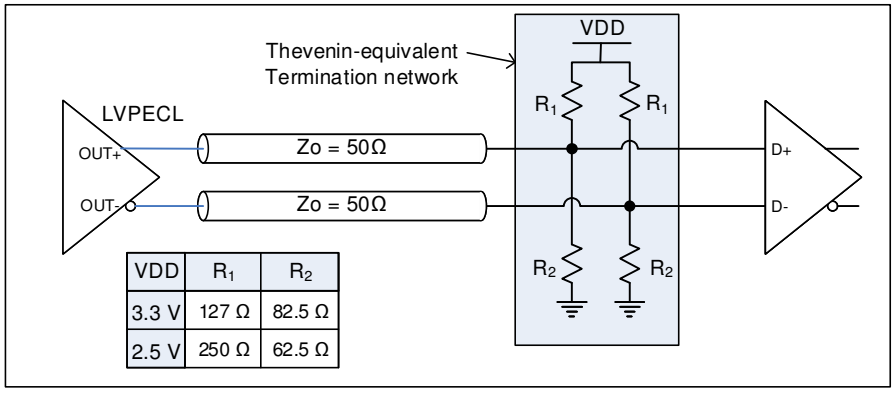


Figure 6: LVPECL DC-coupled load termination with Thevenin equivalent network

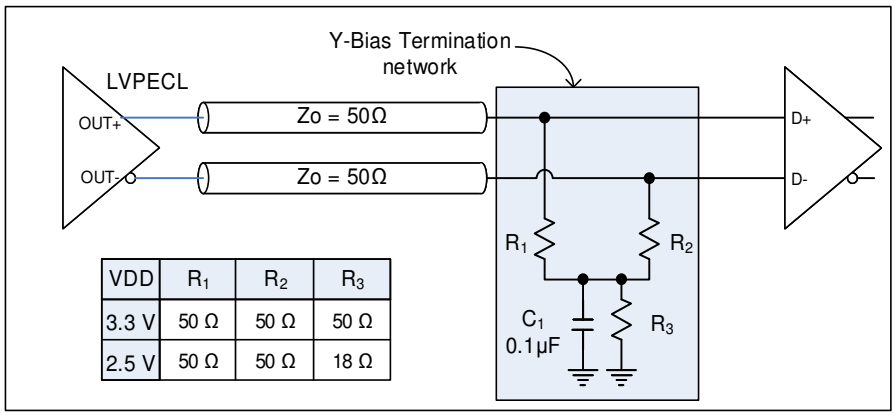


Figure 7: LVPECL with Y-Bias termination

Termination Diagrams (Continued)

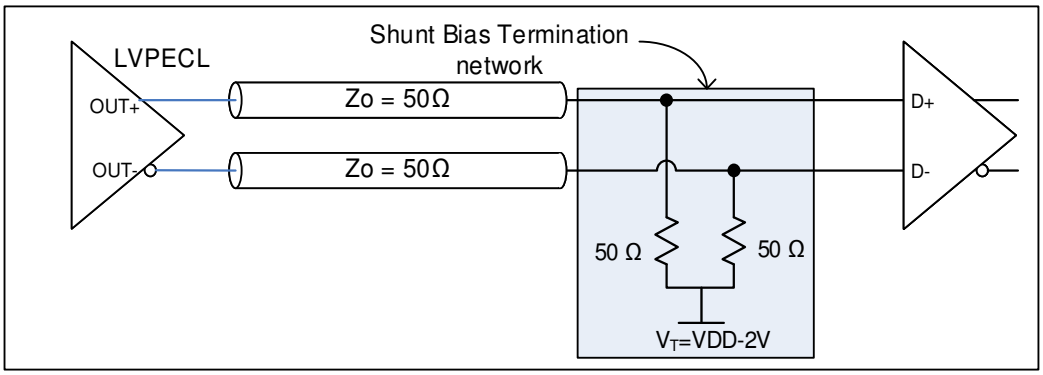


Figure 8: LVPECL with DC-coupled parallel shunt load termination

Termination Diagrams (Continued)

LVDS:

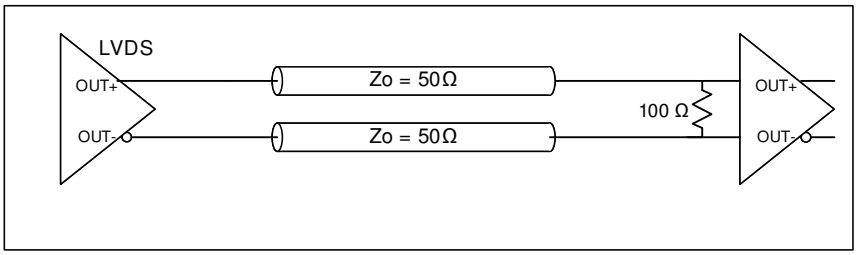


Figure 9: LVDS single DC termination at the load

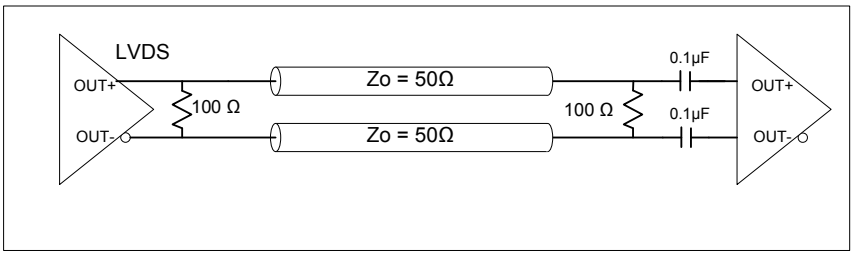


Figure 10: LVDS double AC termination with capacitor close to the load

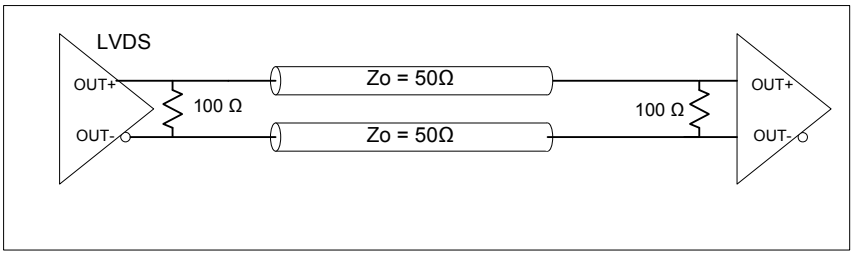


Figure 11: LVDS double DC termination

Termination Diagrams (Continued)

HCSL:

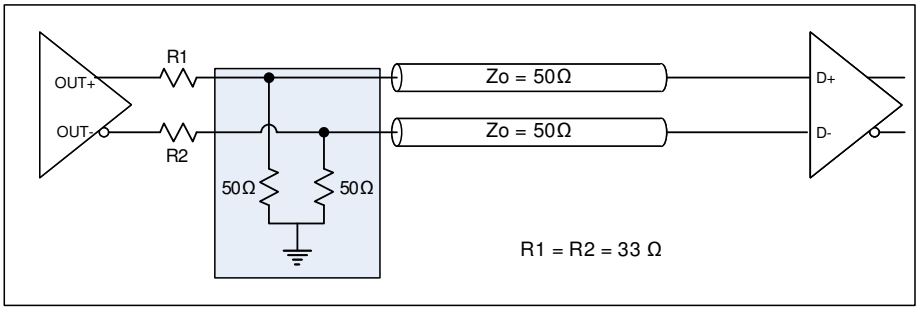
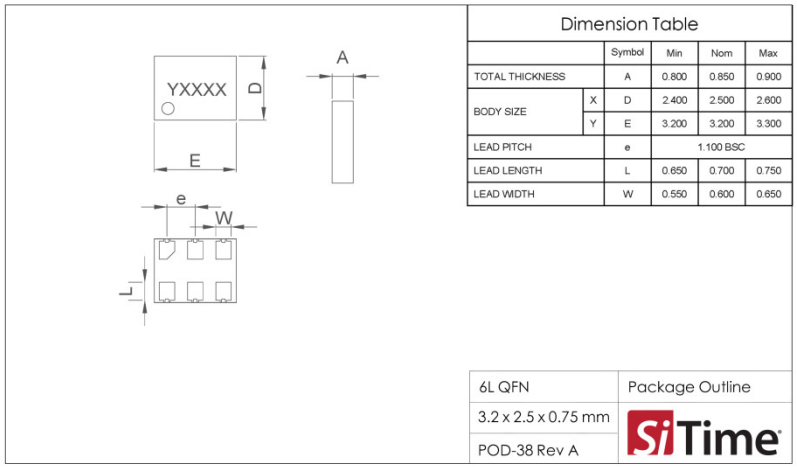


Figure 12: HCSL interface termination

Dimensions and Patterns

Package Size – Dimensions (Unit: mm)[8]	Recommended Land Pattern (Unit: mm)[9]
3.2 x 2.5 x 0.75 mm	**3.2 x 2.5 x 0.75 mm**
7.0 x 5.0 x 0.90 mm[10]	**7.0 x 5.0 x 0.90 mm**[10]

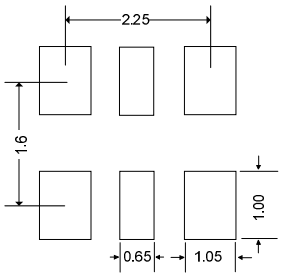
3.2 x 2.5 x 0.75 mm



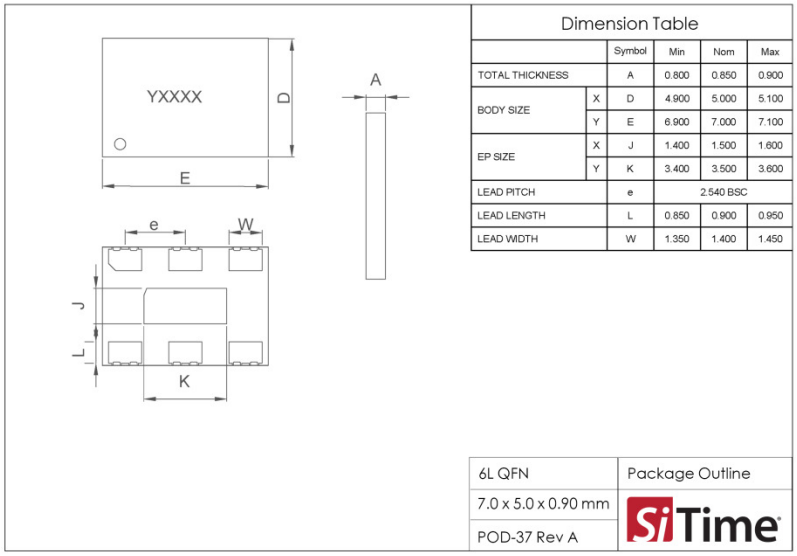
Dimension Table

		Symbol	Min	Nom	Max
TOTAL THICKNESS		A	0.800	0.850	0.900
BODY SIZE	X	D	2.400	2.500	2.600
	Y	E	3.200	3.200	3.300
LEAD PITCH		e	1.100 BSC		
LEAD LENGTH		L	0.650	0.700	0.750
LEAD WIDTH		W	0.550	0.600	0.650

6L QFN	Package Outline
3.2 x 2.5 x 0.75 mm	
POD-38 Rev A	



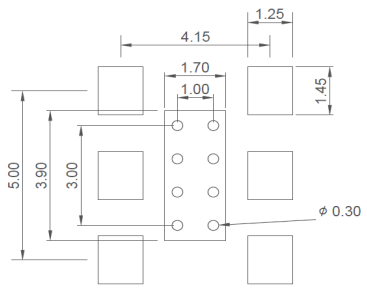
7.0 x 5.0 x 0.90 mm[10]



Dimension Table

		Symbol	Min	Nom	Max
TOTAL THICKNESS		A	0.800	0.850	0.900
BODY SIZE	X	D	4.900	5.000	5.100
	Y	E	6.900	7.000	7.100
EP SIZE	X	J	1.400	1.500	1.600
	Y	K	3.400	3.500	3.600
LEAD PITCH		e	2.540 BSC		
LEAD LENGTH		L	0.850	0.900	0.950
LEAD WIDTH		W	1.350	1.400	1.450

6L QFN	Package Outline
7.0 x 5.0 x 0.90 mm	
POD-37 Rev A	

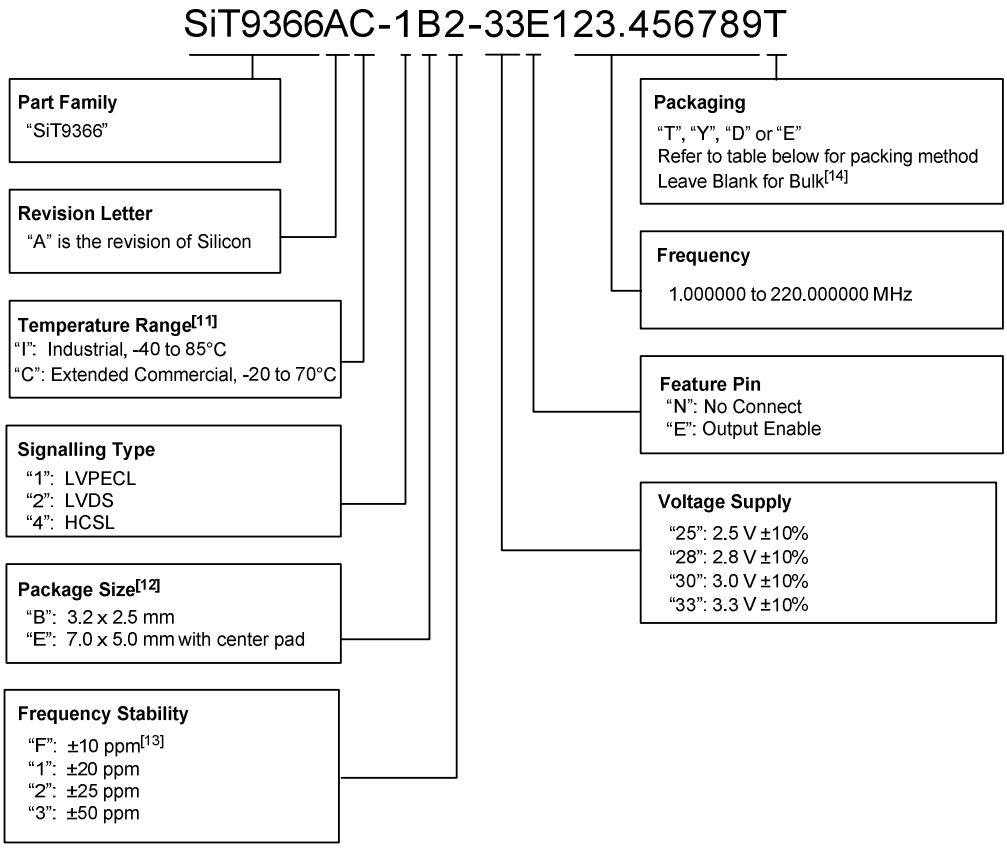


Note:
Circles in center pad are thermal vias, recommended to improve thermal performance

Notes:

8. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.
9. A capacitor of value 0.1 µF or higher between Vdd and GND is required. An additional 10 µF capacitor between Vdd and GND is required for the best phase jitter performance
10. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.

Ordering Information



Notes:

11. Contact SiTime for higher temperature range options
12. Contact SiTime for 5.0 x 3.2 mm package
13. Contact SiTime for ± 10 ppm option
14. Bulk is available for sampling only

Table 10. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	—	—	—	—	T	Y
3.2 x 2.5	D	E	T	Y	—	—

Table 11. Revision History

Revision	Release Date	Change Summary
1.0	09/06/2017	Final release

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